

Data Sheet January 2000 File Number 2934.3

15A, 1000V Ultrafast Dual Diode

The RURH15100CC is an ultrafast dual diode with soft recovery characteristics ($t_{rr} < 100$ ns). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheel/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

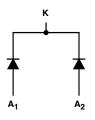
Formerly developmental type TA09906.

Ordering Information

PART NUMBER	PACKAGE	BRAND	
RURH15100CC	TO-218AC	URH15100C	

NOTE: When ordering, use the entire part number.

Symbol



Features

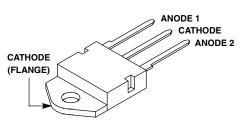
- · Avalanche Energy Rated
- · Planar Construction

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- · General Purpose

Packaging

JEDEC TO-218AC



Absolute Maximum Ratings (Per Leg) T_C = 25°C, Unless Otherwise Specified RURH15100CC UNITS 1000 Working Peak Reverse VoltageV_{RWM} 1000 ٧ DC Blocking Voltage V_R 1000 ٧ 15 Α $(T_C = 142^{\circ}C)$ Repetitive Peak Surge CurrentIFRM 30 Α (Square Wave 20kHz) 200 Α (Halfwave, 1 Phase 60Hz) 100 W 20 mJ οС -65 to 175

RURH15100CC

Electrical Specifications (Per Leg) T_C = 25°C, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	
V _F	I _F = 15A	-	-	1.8	V
	I _F = 15A, T _C = 150 ^o C	-	-	1.5	V
I _R	V _R = 1000V	-	-	100	μΑ
	V _R = 1000V, T _C = 150 ^o C	-	-	500	μΑ
t _{rr}	$I_F = 1A$, t $dI_F/dt = 100A/\mu s$	-	-	100	ns
	$I_F = 15A$, t $dI_F/dt = 100A/\mu s$	-	-	125	ns
ta	$I_F = 15A$, t $dI_F/dt = 100A/\mu s$	-	75	-	ns
t _b	$I_F = 15A$, t $dI_F/dt = 100A/\mu s$	-	40	-	ns
$R_{ heta JC}$		-	-	1.5	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time at dI_F/dt = 100A/ μ s (See Figure 6), summation of t_a + t_b .

 t_a = Time to reach peak reverse current at dI_F/dt = 100A/ μ s (See Figure 6).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

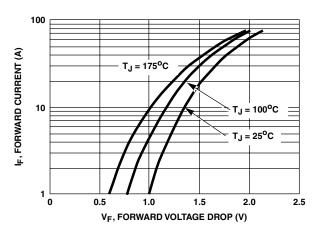


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

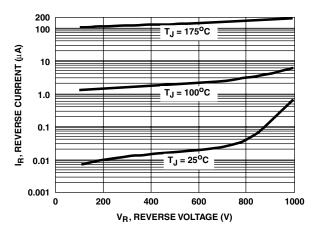


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

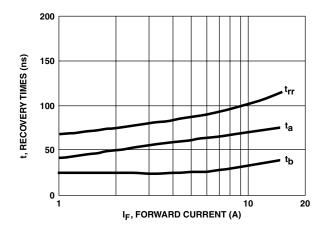


FIGURE 3. t_{rr} , t_a and t_b curves vs forward current

16 I_{F(AV)}, AVERAGE FORWARD CURRENT (A) DC 14 12 SQUARE WAVE 10 8 6 4 2 0 120 130 140 150 160 170 180 T_C, CASE TEMPERATURE (°C)

FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

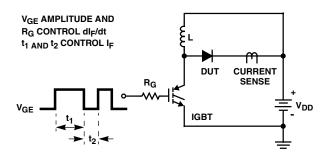


FIGURE 5. t_{rr} TEST CIRCUIT

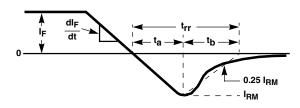


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

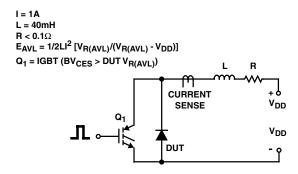


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

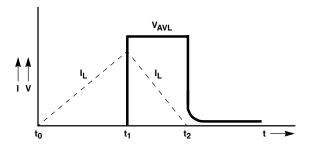


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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DenseTrench™	HiSeC™	QS™	TinyLogic™
DOME™	ISOPLANAR™	QT Optoelectronics™	UHC TM
EcoSPARK™	LittleFET™	Quiet Series™	UltraFET™
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